EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/532118	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/07 21:39
S2	1237	(438/95).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/10/07 21:40
S3	165	(257/226).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/10/07 21:40
S5	5	(("4945243") or ("4369458") or ("20020024016") or ("6215123") or ("6046068")).PN.	US-PGPUB; USPAT	OR	OFF	2009/10/07 21:44
S6	6	(("4945243") or ("4369458") or ("20020024016") or ("6215123") or ("6046068") or ("20040069213")).PN.	US-PGPUB; USPAT	OR	OFF	2009/10/14 08:30
S7	104	(radiation adj detector adj cell)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/14 08:41
S8	24	S7 and (semiconductor adj substrate) and conduct$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/14 08:42
S9	18	S7 and (semiconductor adj substrate) and conduct$3 and @ad<="20031023"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/14 08:42
S10	1	("7381594").PN.	USPAT	OR	OFF	2009/10/26 06:21

S11	8	"6380528"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/26 06:59
S12	1	("6380528").PN.	US-PGPUB; USPAT	OR	OFF	2009/10/26 07:00
S13	43	puhakka.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 22:13
S14	8	S13 and kimmo	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 22:14
S15	1227	(438/57).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:16
S16	157	257/E21.617.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/11 22:16
S17	127	(438/84).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:17
S18	876	(438/98).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:17
S19	1693	(438/102).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:17

S20	107	(438/930).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:17
S21	341	(438/958).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:18
S22	2286	(438/128).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:18
S23	67	(438/83).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/11 22:18
S24	55	(("4,106,046") or ("4,142,199") or ("4,188,709") or ("4,239,312") or ("4,257,057") or ("4,513,312") or ("4,602,289") or ("4,609,823") or ("4,694,316") or ("4,744,057") or ("4,811,371") or ("4,817,123") or ("4,873,708") or ("4,900,943") or ("4,916,664") or ("4,947,258") or ("4,992,878") or ("5,012,247") or ("5,043,582") or ("5,081,346") or ("5,113,263") or ("5,149,954") or ("5,153,420") or ("5,168,528") or ("5,182,624") or ("5,245,191") or ("5,291,402") or ("5,315,114") or ("5,315,147") or ("5,315,411") or ("5,379,336") or ("5,401,952") or ("5,402,168") or	US-PGPUB; USPAT	OR	OFF	2010/03/14 21:51

		("5,475,212") or ("5,526,394") or ("5,587,738") or ("5,596,200") or ("5,742,058") or ("5,812,191") or ("5,917,881") or ("5,937,326") or ("5,998,777") or ("6,014,313") or ("6,035,013") or ("6,248,990") or ("6,262,421") or ("6,278,181") or ("6,459,077") or ("6,563,539") or ("6,645,787") or ("6,952,042") or ("20020036269") or ("20020130266") or ("20020180063") or ("20030155516")).PN.				
S25	1178	(438/669).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/14 22:08
S26	4230	257/E21.577.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:08
S27	1900	257/E21.001.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:10
S28	19404	(semiconductor adj substrate) and (first adj (conduct$4 or metal)) and (second adj (conduct$4 or metal)) and (etch$3 or remov$3) and ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) and expos$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:21

S29	2825	((semiconductor adj substrate) and (first adj (conduct$4 or metal)) and (second adj (conduct$4 or metal)) and (etch$3 or remov$3) and ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) and expos$3).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:21
S30	878	((semiconductor adj substrate) same (first adj (conduct$4 or metal)) same (second adj (conduct$4 or metal)) same (etch$3 or remov$3) same ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) same expos$3).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:22
S31	0	((semiconductor adj substrate) same (first adj (conduct$4 or metal)) same (second adj (conduct$4 or metal)) same (etch$3 or remov$3) same ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) same expos$3) and (radiat$3 adj (device or structure or detector))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:23
S32	0	(((semiconductor adj substrate) same (first adj (conduct$4 or metal)) same (second adj (conduct$4 or metal)) same (etch$3 or remov$3) same ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) same expos$3) and (radiat$3 adj (device or structure or detector))).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:23
S33	71	((semiconductor adj substrate) and (first adj (conduct$4 or metal)) and (second adj (conduct$4 or metal)) and (etch$3 or remov$3) and ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) and expos$3) and (radiat$3 adj (device or structure or detector))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:24

S34	2	(((semiconductor adj substrate) and (first adj (conduct$4 or metal)) and (second adj (conduct$4 or metal)) and (etch$3 or remov$3) and ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) and expos$3) and (radiat$3 adj (device or structure or detector))).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:25
S35	9	"250"/$.ccls. and ((semiconductor adj substrate) and (first adj (conduct$4 or metal)) and (second adj (conduct$4 or metal)) and (etch$3 or remov$3) and ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) and expos$3) and (radiat$3 adj (device or structure or detector))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:26
S36	1657	257/E21.131.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:29
S37	1361012	H01L021/$.ipc. OR H01L21/$.ipcr.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:30
S38	16	S37 and ((semiconductor adj substrate) and (first adj (conduct$4 or metal)) and (second adj (conduct$4 or metal)) and (etch$3 or remov$3) and ((oxide or insulat$4 or dielectric or passivation) adj (layer or film)) and expos$3) and (radiat$3 adj (device or structure or detector))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/03/14 22:30
S39	2455	(438/22).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/14 22:31

S40	420	(438/25).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/14 22:31
S41	977	(438/26).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/14 22:31
S42	663	(438/27).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/14 22:32
S43	1932	(438/29).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/03/14 22:32

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